

**IGBT Modules** 

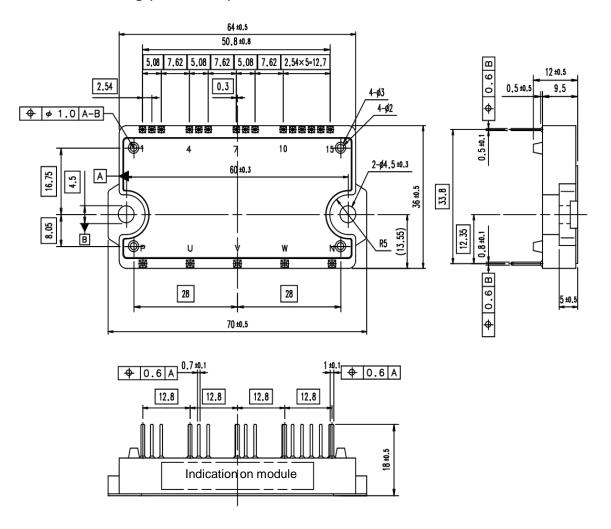
### IGBT Module (X series) 1200V / 10A / IPM

#### ■ Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- ·Low power loss and soft switching
- •High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit



### ■ Outline drawing (Unit:mm)



Weight:55g(typ.)

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#### ■ Absolute maximum ratings

 $T_{\rm C}$ =25°C,  $T_{\rm vi}$ =25°C,  $V_{\rm CC}$ =15V unless otherwise specified

	Items	Symbol	Conditions	Min.	Max.	Units
Cd	ollector-emitter voltage	$V_{CES}$	*1	-	1200	V
Sh	ort circuit voltage	$V_{\rm SC}$	*2	400	800	V
_		I <sub>C</sub>	DC	-	10	Α
¥	Collector current	I <sub>CP</sub>	1ms	-	20	Α
Inverte		-1 <sub>C</sub>	Duty=100% *3	-	10	Α
Ľ	Total power dissipation	$P_{\text{tot}}$	IGBT 1 device *4	-	108	W
	Collector current	$I_{C}$	DC	-	-	Α
ş	Collector current	I <sub>CP</sub>	1ms	-	-	Α
Brake	Forward current of diode	I <sub>F</sub>		-	-	Α
٦	Total power dissipation	$P_{\text{tot}}$	IGBT 1 device *4	-	-	W
Sι	pply voltage of pre-driver	V <sub>cc</sub>	*5	-0.5	20	V
Inp	out signal voltage	$V_{in}$	*6	-0.5	$V_{\rm CC} + 0.5$	V
Ala	arm signal voltage	$V_{ALM}$	*7	-0.5	$V_{\rm CC}$	V
Ala	arm signal current	I <sub>ALM</sub>	*8	-	20	mΑ
Vii	tual junction temperature	$T_{vj}$		-	175	°C
Op	perating virtual junction temperature	$T_{\rm vjop}$		-	150	°C
Or	perating case temperature	$T_{c}$		-20	125	°C
St	orage temperature	$T_{ m stg}$		-40	125	°C
Sc	lder temperature	$T_{sol}$	*9	-	260	°C
lsc	olating voltage	$V_{isol}$	*10	-	2500	Vrms
Mo	ounting torque of screws to heat sink	Ms	Mounting(M4)	-	1.7	Nm
	ounting torque of screws to terminals	$M_{\rm t}$	Main terminals(M4)	-	-	Nm
M	otos			-	•	

- \*1: V<sub>CES</sub> shall be applied to the input voltage between terminal P-(U,V, W) and (U,V, W)-N.
- \*2: In the case of the load inductance to be over 1µH.
- \*3: Duty=150°C/ $R_{th(i-c)}/(I_F \times V_F \text{ Max.}) \times 100$

- \*4:  $P_{\text{tot}}$ =150°C/ $R_{\text{th(i-c)}}$ \*5:  $V_{\text{CC}}$  shall be applied to the input voltage between terminal No.3 and 1, 6 and 4, 9 and 7,11 and 10.
  \*6:  $V_{\text{in}}$  shall be applied to the input voltage between terminal No.2 and 1, 5 and 4, 8 and 7,12~14 and 10.
- \*7: V<sub>ALM</sub> shall be applied to the voltage between terminal No.15 and 10.
- \*8: I<sub>ALM</sub> shall be applied to the input current to terminal No.15.
- \*9: Immersion time 10±1sec. 1time
- \*10: Terminal to base, 50/60Hz sine wave 1min. All terminals should be connected together during the test.

#### **■** Electrical characteristics

#### Main circuit

 $T_{\rm vj}$ =25°C,  $V_{\rm CC}$ =15V unless otherwise specified

	Item	Symbol	Co	nditions	3	Min.	Тур.	Max.	Units
er	Collector current at off signal Input	I <sub>CES</sub>	V <sub>CE</sub> = 1200V			ı	1	1.0	mA
Inverter	Collector-emitter	$V_{\scriptscriptstyle{CE(sat)}}$	$I_{\rm C}$ = 10A		Terminal	-		2.25	V
≥	saturation voltage	• CE(sai)			Chip	-	2.05	-	V
=	Forward voltage of FWD	$V_{\scriptscriptstyle \sf F}$	$I_{\rm F}$ = 10A		Terminal	ı	ı	2.60	V
	Torward voltage of T VVD	V F			Chip	-	2.25	-	V
	Collector current at off signal Input	I <sub>CES</sub>	V <sub>CE</sub> =-V						mA
Brake	Collector-emitter	$V_{\scriptscriptstyle{CE(sat)}}$	$I_{\rm C} = -A$		Terminal	ı	ı	-	V
l ‰	saturation voltage	CE(sat)			Chip	ı	ı	-	V
"	Forward voltage of FWD	$V_{\scriptscriptstyle \sf F}$	$I_{\rm F} = -A$		Terminal	ı	ı	-	V
	Torward voltage of TWD	VF			Chip	ı	ı	-	V
Switcl	ning time	$t_{\sf on}$	$I_{\rm C}$ = 10A	$T_{vi}=1$	50°C	0.5	ı	-	μs
*11		$t_{\sf d(on)}$	$V_{DC} = 600 V$			0.5	ı		μs
		$t_{ m off}$				ı	ı	2.4	μs
		$t_{\sf d(off)}$				-	-	2.2	μs
		$t_{\rm rr}$	$I_{\rm F} = 10A$ $V_{\rm DC} = 600V$	$T_{\rm vi}$ =15	50°C	-	-	0.5	μs
			- DC 3001						

<sup>\*11:</sup> Turn on time  $(t_{on}) = t_{d(on)} + t_r$ , Turn off time  $(t_{off}) = t_{d(off)} + t_f$ 

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#### Control circuit

 $T_{\rm vj}$ =25°C,  $V_{\rm CC}$ =15V unless otherwise specified

ltem	Symbol	Conditions		Min.	Тур.	Max.	Units
Supply current of P-side	I <sub>ccp</sub>	Switching frequency $(f_{SW}) = 0 \sim T_C = -20 \sim 125$ °C	15kHz	-	-	7	mA
pre-driver (per one unit)	·	1 <sub>C</sub> = -20~125 C					
Supply current of N-side	I <sub>con</sub>			-	-	19	mΑ
pre-driver	- CCII						
Input signal threshold voltage	$V_{inth(on)}$	V <sub>in</sub> -GND	ON	1.2	1.4	1.6	V
	$V_{\text{inth(off)}}$	V in-OIVD	OFF	1.5	1.7	1.9	V

#### Protection circuit

 $T_{v_i}$ =25°C,  $V_{CC}$ =15V unless otherwise specified

Item	Symbol	Conditions		Min.	Тур.	Max.	Units
Over current Inverter	ı	T <sub>vi</sub> =150°C		15	-	-	Α
protection level Brake	I <sub>oc</sub>			-	-	-	Α
Over current protection delay time	$t_{ ext{dOC}}$	T <sub>vi</sub> =150°C		•	4.0	-	μs
Short circuit protection delay time	$t_{ t dSC}$	T <sub>vi</sub> =150°C		-	2.0	-	μs
IGBT chips over heating	$T_{jOH}$	Surface of IGBT Chips		175	-	-	°C
protection temperature level	<b>7</b> jOH						
Over heating protection hysteresis	$T_{\rm iH}$			•	20	-	°C
Under voltage protection level	$V_{\scriptscriptstyle UV}$			11.0	-	12.5	V
Under voltage protection hysteresis	$V_{\scriptscriptstyle H}$			0.2	0.5	-	V
	$t_{\text{ALM(OC)}}$	ALM-GND		1.0	2.0	2.4	ms
Alarm signal hold time	$t_{ALM(UV)}$	T <sub>C</sub> =-20∼125°C	V <sub>cc</sub> ≧10V	3.5	4.0	4.5	ms
	$t_{\text{ALM(TjOH)}}$			7.0	8.0	9.0	ms
Alarm signal voltage	$V_{\scriptscriptstyle ALMH}$	ALM-GND, without protection	)	14.5	-	15.0	V
Resistance for current limit	$R_{\scriptscriptstyle ALM}$			960	-	1570	Ω

### ■ Thermal resistance characteristics ( $T_c = 25^{\circ}C$ )

ltem			Symbol	Min.	Тур.	Max.	Units
Thermal resistance	Inverter	RC-IGBT	$R_{ m th(j-c)}$	-	-	1.38	K/W K/W
junction to case	Droko	IGBT	$R_{th(j-c)Q}$	-	-	-	K/W
*12	Brake	FWD	$R_{th(j-c)D}$	-	-	-	K/W
Thermal resistance case to heat sink *13			$R_{th(c-s)}$	-	0.05	-	K/W

<sup>\*12:</sup> For 1 device, the measurement point of the case is just under the chip.

### ■ Noise immunity (V<sub>DC</sub>=600V, VCC=15V)

ltem	Conditions	Min.	Тур.	Max.	Units
Common mode	Pulse width 1µs,polarity ±,10min.	<b>+</b> 2 0	_	_	kV
rectangular noise	Judge: no over-current, no miss operating	±2.0		_	ΚV

### ■ Recommended operating conditions

Item	Symbol	Min.	Тур.	Max.	Units
DC bus voltage	$V_{ exttt{DC}}$	-	-	800	V
Power supply voltage of pre-driver	V <sub>cc</sub>	13.5	15.0	16.5	V
Switching frequency of IPM	$f_{\scriptscriptstyle{SW}}$	-	-	20.0	kHz
Arm shoot through blocking time for IPM's input signal *14	$t_{\scriptscriptstyle \sf dead}$	1.9	-	-	μs
Screw torque (M4)	-	1.3	-	1.7	Nm

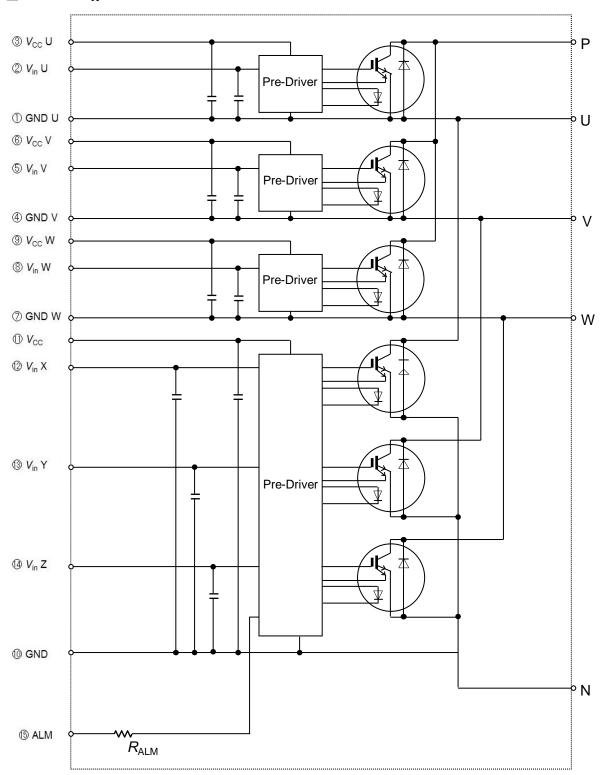
<sup>\*14:</sup>  $t_{\text{dead}} = t_{\text{off}} - t_{\text{d(on)}}$ 

<sup>\*13:</sup> This is the value which is defined mounting on the additional heat sink with 1 W/(m·K) thermal grease.



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#### ■ Block diagram



Pre-drivers include following functions

- 1. Amplifier for driver
- 2. Short circuit protection
- 3. Under voltage lockout circuit
- 4. Over current protection
- 5. IGBT chip over heating protection

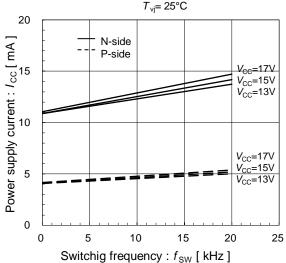


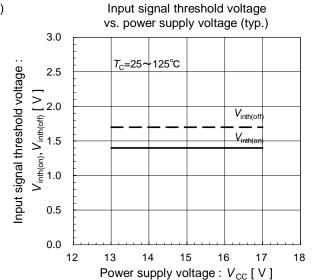
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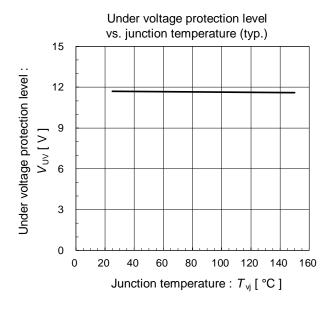
#### ■ Characteristics (representative)

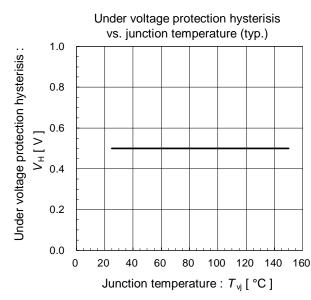
#### Control circuit

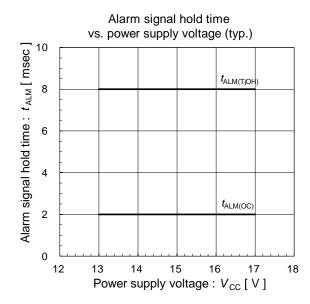
Power supply current vs. switching frequency (typ.)

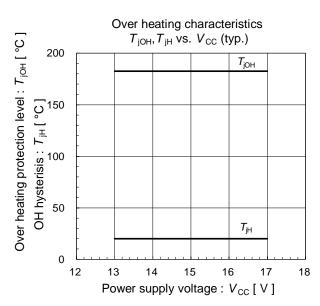






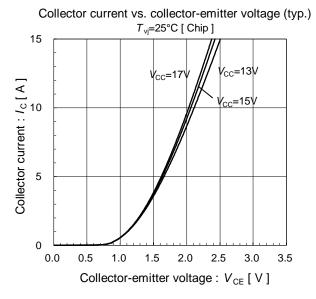


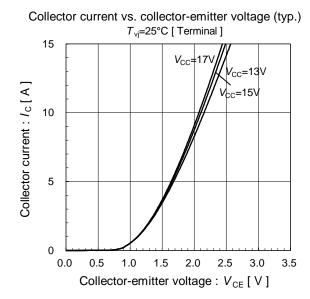


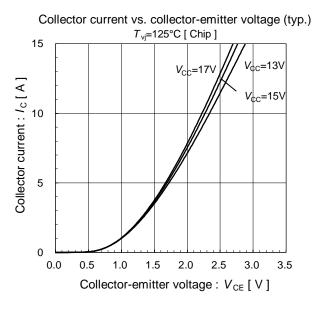


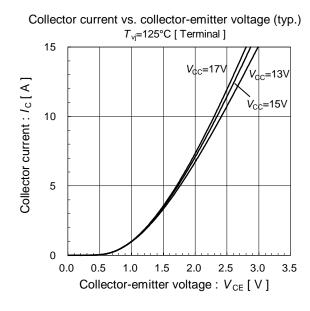
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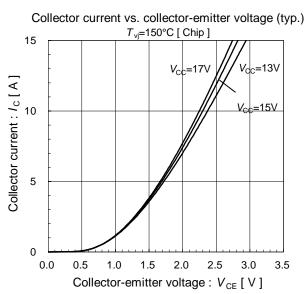
#### Inverter

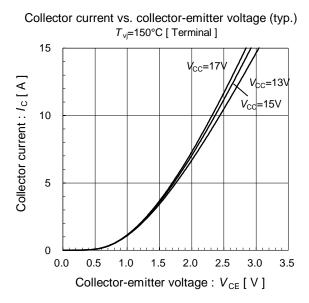




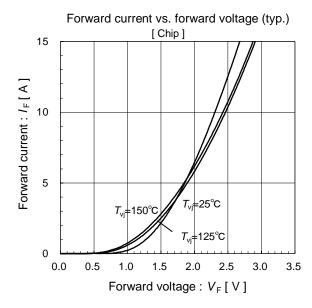


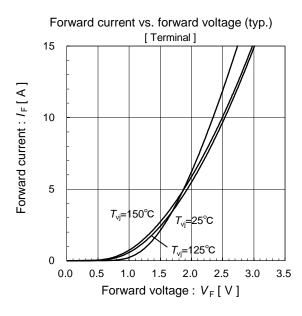


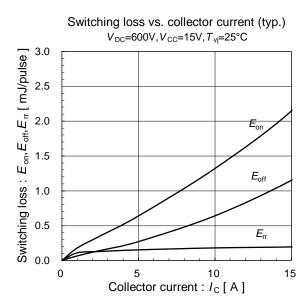


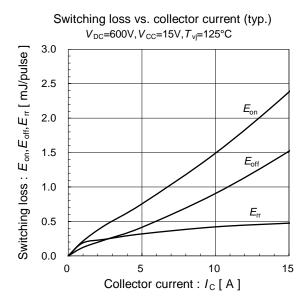


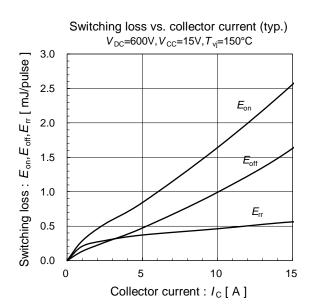




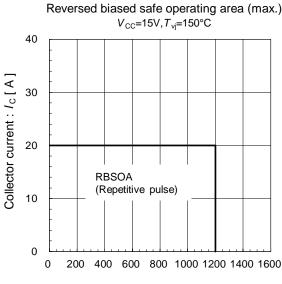


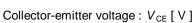


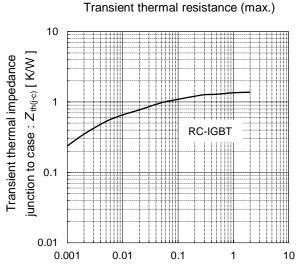




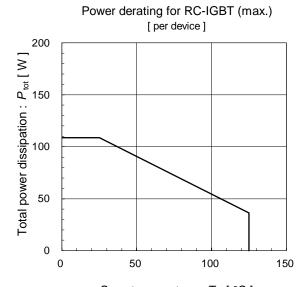






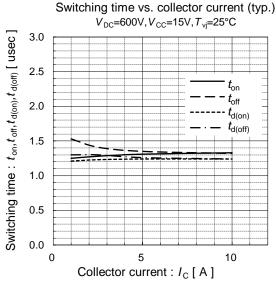


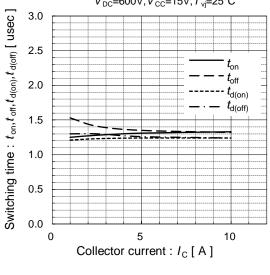
Pulse width :  $P_{W}$  [ sec ]

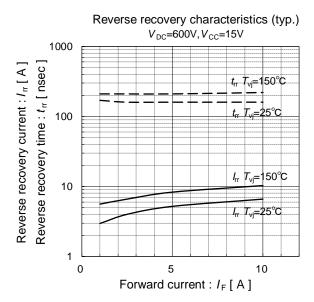


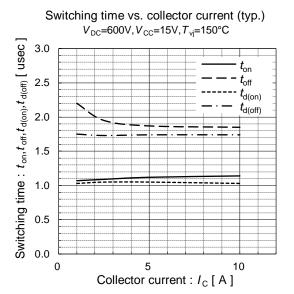
Case temperature :  $T_{C}$  [ °C ]

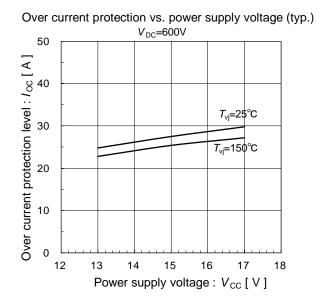














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